





#### P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

#### **Features**

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 2)
- ESD Protected Gate
- "Green" Device (Note 4)
- Qualified to AEC-Q101 standards for High Reliability

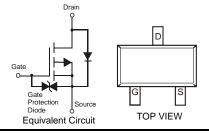
### **Mechanical Data**

- Case: SOT-523
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.002 grams (approximate)









# **Maximum Ratings** $@T_A = 25^{\circ}C$ unless otherwise specified

Chara	acteristic		Symbol	Value	Units	
Drain-Source Voltage			V <sub>DSS</sub>	-20	V	
Gate-Source Voltage			$V_{GSS}$	±8	V	
Drain Current (Note 1)	Steady State	$T_A = 25$ °C $T_A = 85$ °C	I <sub>D</sub>	-430 -310	mA	
Pulsed Drain Current (Note 3)			I <sub>DM</sub>	-750	mA	

#### Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	$P_D$	150	mW
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	833	°C/W
Operating and Storage Temperature Range	$T_{J,}T_{STG}$	-55 to +150	°C

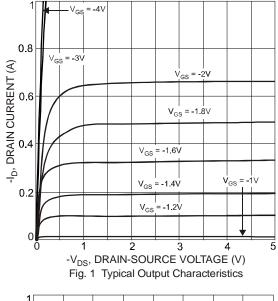
# Electrical Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 5)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	_		V	$V_{GS} = 0V, I_D = -250mA$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>		_	-1.0	μΑ	$V_{DS} = -20V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±1.0	μА	$V_{GS} = \pm 4.5V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.5	_	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
			0.7	1.1		$V_{GS} = -4.5V$ , $I_{D} = -430mA$	
Static Drain-Source On-Resistance	R <sub>DS</sub> (ON)	_	1.1	1.6	Ω	$V_{GS} = -2.5V$ , $I_D = -300mA$	
			1.7	2.4		$V_{GS} = -1.8V, I_{D} = -150mA$	
Forward Transfer Admittance	Y <sub>fs</sub>	200	_	_	ms	$V_{DS} = 10V, I_D = 0.2A$	
Diode Forward Voltage (Note 5)	$V_{SD}$	_	_	-1.4	V	$V_{GS} = 0V, I_{S} = -115mA$	
DYNAMIC CHARACTERISTICS							
Input Capacitance	C <sub>iss</sub>	_	_	175	pF	101/1/	
Output Capacitance	Coss		_	30	pF	$V_{DS} = -16V, V_{GS} = 0V$ - f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	_	20	pF	1 = 1.0WH IZ	

Notes: 1. Device

- Device mounted on FR-4 PCB.
  No purposefully added lead.
- Pulse width ≤10μS, Duty Cycle ≤1%
- 4. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.
- 5. Short duration pulse test used to minimize self-heating effect.





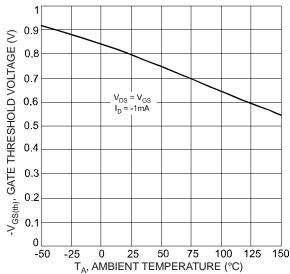


Fig. 3 Gate Threshold Voltage vs. Ambient Temperature

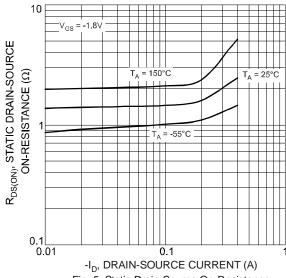
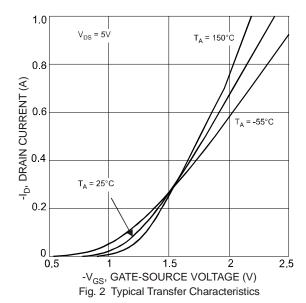


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current



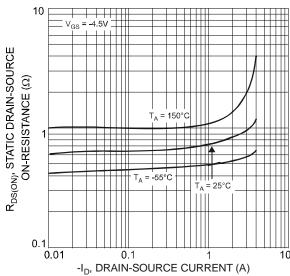


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

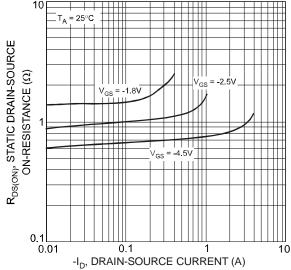


Fig. 6 Static Drain-Source On-Resistance vs. Drain-Source Current



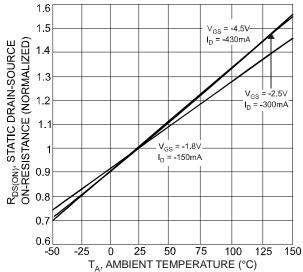


Fig. 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

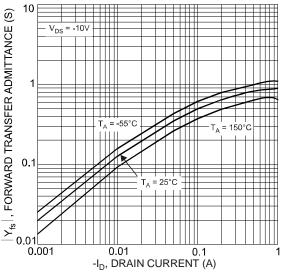


Fig. 9 Forward Transfer Admittance vs. Drain Current

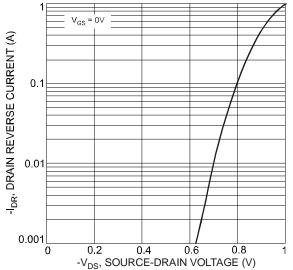
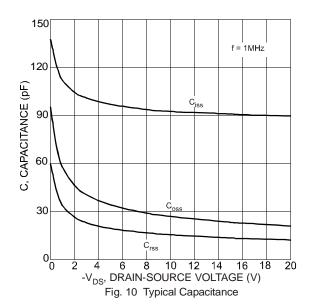


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

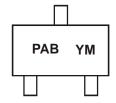


# Ordering Information (Note 6)

Ī	Part Number	Case	Packaging
	DMP2004TK-7	SOT-523	3000/Tape & Reel

Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

# Marking Information



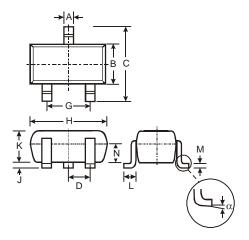
PAB = Product Type Marking Code YM = Date Code Marking Y = Year (ex: T = 2006) M = Month (ex: 9 = September)

Date Code Key

Year	200	6	2007		2008	20	09	2010		2011	2	2012
Code	Т		U		V	V	٧	Χ		Υ		Z
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

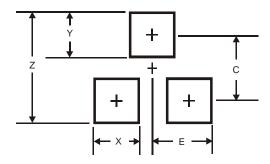


### **Package Outline Dimensions**



SOT-523						
Dim	Min	Max	Тур			
Α	0.15	0.30	0.22			
В	0.75	0.85	0.80			
С	1.45	1.75	1.60			
D	_	_	0.50			
G	0.90	1.10	1.00			
Н	1.50	1.70	1.60			
7	0.00	0.10	0.05			
K	0.60	0.80	0.75			
L	0.10	0.30	0.22			
М	0.10	0.20	0.12			
N	0.45	0.65	0.50			
α	0°	8°	_			
All Dimensions in mm						

# **Suggested Pad Layout**



Dimensions	Value (in mm)
Z	1.8
Х	0.4
Y	0.51
С	1.3
E	0.7

#### IMPORTANT NOTICE

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